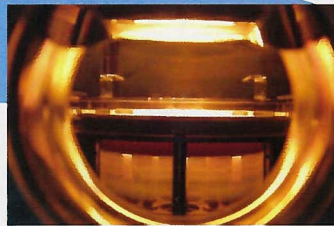




**TAIYO NIPPON SANSO**  
The Gas Professionals

# STA series |

Annealing Reactor with High-Performance GaN  
MOCVD System for AlN/AlGaN Growth



## STA-1800 Specifications

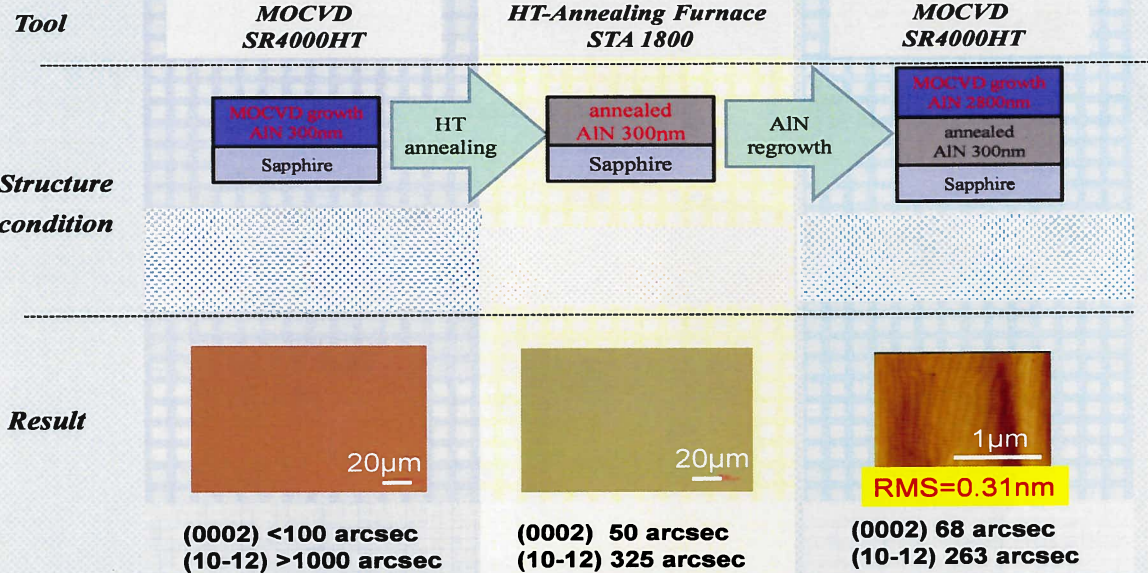
1. Wafer : 2", 4" and 6"(under development)
2. Heating : up to **1800°C**

## SR4000HT Specifications

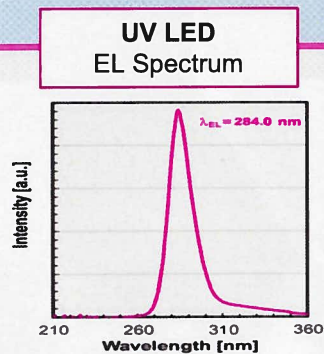
1. Wafer Size : 4" × 1, 2" × 3
2. Heating : up to **1350°C**
3. Growth at 10 kPa –100 kPa



## 【Development of high-quality AlN buffer layer】

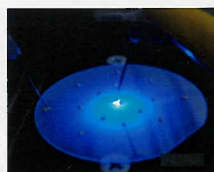
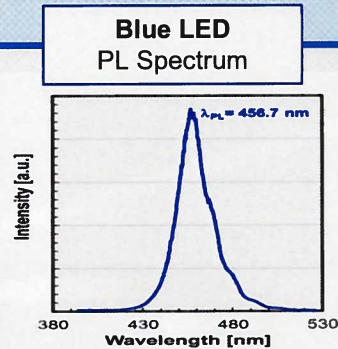


## 【Performance of Light emitting device by SR4000HT】

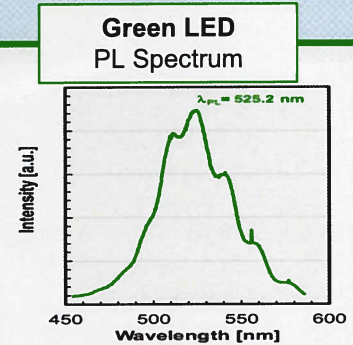


\*Collaboration with ITRI  
(Industrial Technology Research  
Institute of Taiwan)

**IQE : 65%**  
30kPa Growth



**IQE : 68%**  
Atmospheric  
(100kPa) growth



**IQE : 37%**  
Atmospheric  
(100kPa) growth

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<http://www.mocvd.jp>

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